

CMS16P06D-HF

P-Channel

RoHS Device

Halogen Free

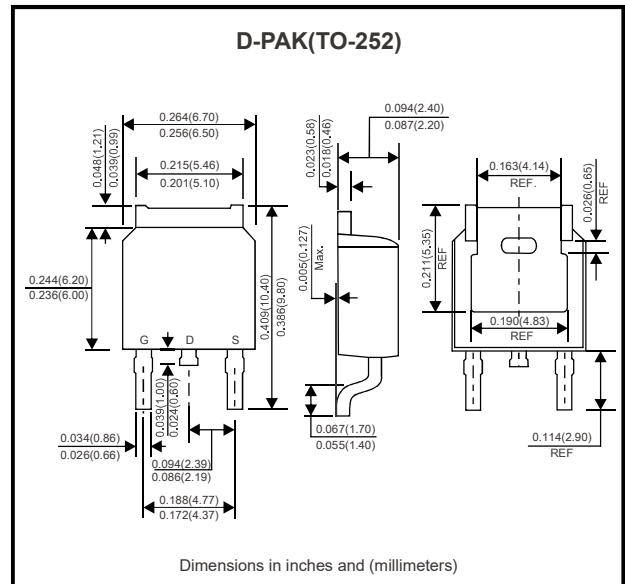


Features

- High Switching Speed
- Low Gate Charge
- Green Device Available
- Low Reverse Transfer Capacitance
- Improved dv/dt Capability
- 100% EAS Guaranteed

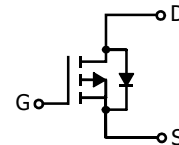
Description

The CMS16P06D is the highest performance P-ch MOSFETs with super high dense cell design for extremely low $R_{DS(ON)}$ and gate charge for most of the synchronous buck converter applications. The CMS16P06D meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.



Circuit diagram

- G : Gate
- D : Drain
- S : Source



Maximum Ratings (at $T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Ratings	Unit
Drain-Source Voltage	V_{DS}	-60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ¹	$I_D @ T_C=25^\circ\text{C}$	-16	A
	$I_D @ T_C=100^\circ\text{C}$	-10	A
Pulsed Drain Current ^{1,2}	$I_{DM} @ T_C=25^\circ\text{C}$	-64	A
Continuous Drain Current	$I_D @ T_A=25^\circ\text{C}$	-5.0	A
	$I_D @ T_A=70^\circ\text{C}$	-4.0	A
Total Power Dissipation ⁴	$P_D @ T_C=25^\circ\text{C}$	25	W
	$P_D @ T_A=25^\circ\text{C}$	2	W
Single Pulse Avalanche Energy, $L=0.1\text{mH}^3$	E_{AS}	51	mJ
Single Pulse Avalanche Current, $L=0.1\text{mH}^3$	I_{AS}	-32	A
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 ~ +150	$^\circ\text{C}$

Thermal Data

Parameter	Symbol	Conditions	Max. Value	Unit
Thermal Resistance Junction-ambient ¹	$R_{\theta JA}$	Steady State	62.5	$^\circ\text{C/W}$
Thermal Resistance Junction-case ¹	$R_{\theta JC}$	Steady State	5.0	$^\circ\text{C/W}$

Company reserves the right to improve product design, functions and reliability without notice.

REV:A

Electrical Characteristics (at $T_J=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Drain-Source Breakdown Voltage	BV_{DSS}	-60	-	-	V	$V_{GS}=0$, $I_D=-250\mu\text{A}$
Gate Threshold Voltage	$V_{GS(th)}$	-1.0	-1.7	-2.5	V	$V_{DS}=V_{GS}$, $I_D=-250\mu\text{A}$
Gate-Source Leakage Current	I_{GSS}	-	-	± 100	nA	$V_{GS}=\pm 20\text{V}$
Drain-Source Leakage Current	I_{DSS}	-	-	-1	μA	$V_{DS}=-60\text{V}$, $V_{GS}=0$
Static Drain-Source On-Resistance ²	$R_{DS(on)}$	-	40	48	m Ω	$V_{GS}=-10\text{V}$, $I_D=-8\text{A}$
		-	55	65		$V_{GS}=-4.5\text{V}$, $I_D=-4\text{A}$
Total Gate Charge ²	Q_g	-	22	-	nC	$I_D=-8\text{A}$ $V_{DS}=-30\text{V}$ $V_{GS}=-10\text{V}$
Gate-Source Charge	Q_{gs}	-	4.1	-		
Gate-Drain ("Miller") Charge	Q_{gd}	-	5.2	-		
Turn-on Delay Time ²	$T_{d(on)}$	-	13	-	ns	$V_{DS}=-30\text{V}$ $I_D=-1\text{A}$ $V_{GS}=-10\text{V}$ $R_G=6\Omega$
Rise Time	T_r	-	42	-		
Turn-off Delay Time	$T_{d(off)}$	-	65	-		
Fall Time	T_f	-	16	-		
Input Capacitance	C_{iss}	-	1256	-	pF	$V_{GS}=0\text{V}$ $V_{DS}=-30\text{V}$ $f=1.0\text{MHz}$
Output Capacitance	C_{oss}	-	87	-		
Reverse Transfer Capacitance	C_{rss}	-	59	-		

Guaranteed Avalanche Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Single Pulse Avalanche Energy ⁵	EAS	12.8	-	-	mJ	$V_{DD}=-25\text{V}$, $L=0.1\text{mH}$, $I_{AS}=-16\text{A}$

Source-Drain Diode

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Diode Forward Voltage ²	V_{SD}	-	-0.72	-1.0	V	$I_S=-1\text{A}$, $V_{GS}=0\text{V}$, $T_J=25^{\circ}\text{C}$
Continuous Source Current ^{1,6}	I_S	-	-	-16	A	---

Notes: 1. The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper.

2. The data tested by pulsed, pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.

3. The EAS data shows Max. rating. The test condition is $V_{DD}=-25\text{V}$, $V_{GS}=-10\text{V}$, $L=0.1\text{mH}$, $I_{AS}=-32\text{A}$.

4. The power dissipation is limited by 150°C junction temperature.

5. The Min. value is 100% EAS tested guarantee.

6. The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.

RATING AND CHARACTERISTIC CURVES

Typical Characteristics

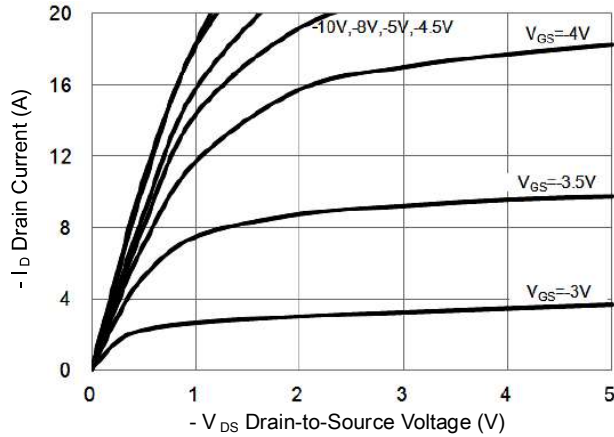


Fig.1 Typical Output Characteristics

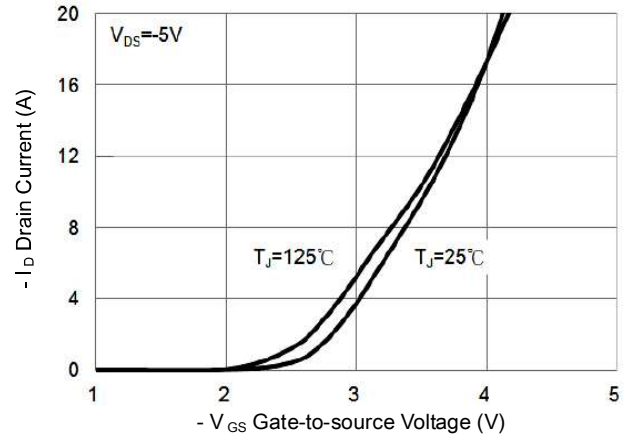


Fig.2 Transfer Characteristics

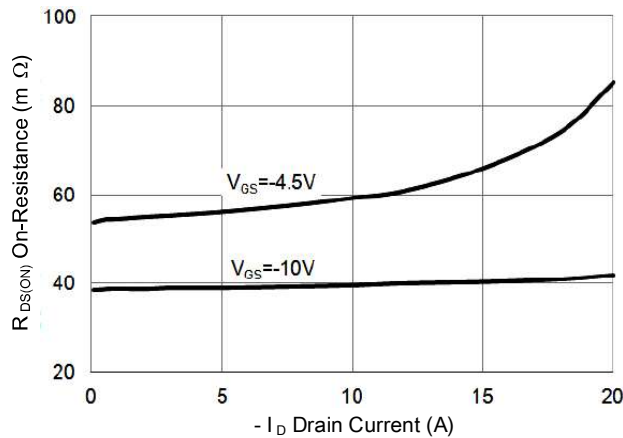


Fig.3 On-Resistance vs. Drain Current

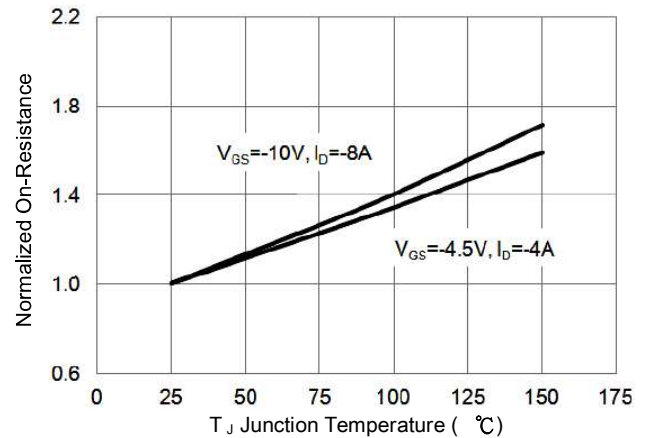


Fig.4 Normalized $R_{DS(ON)}$ vs. T_J

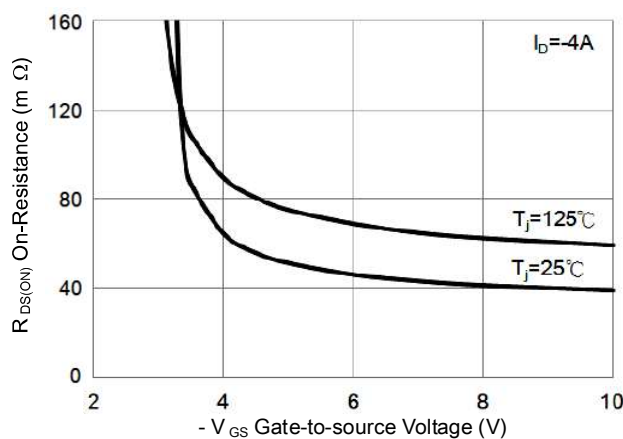


Fig.5 On-Resistance vs. G-S Voltage

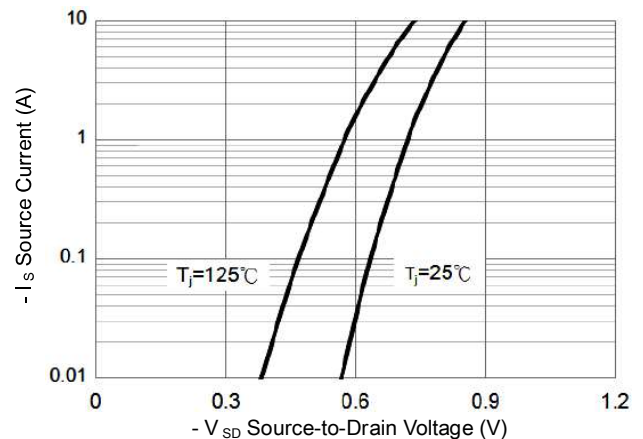


Fig.6 Forward Characteristics of Reverse

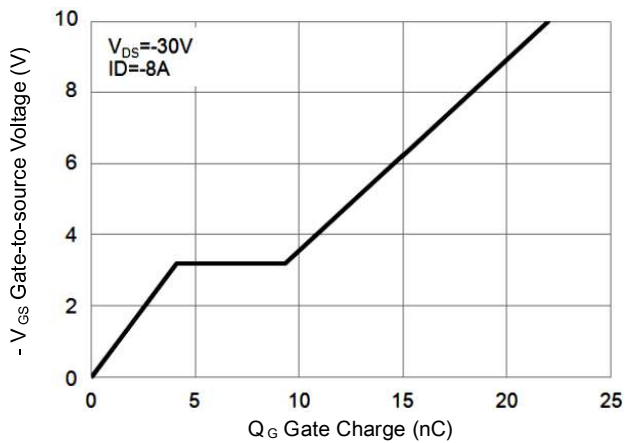


Fig.7 Gate Charge Characteristics

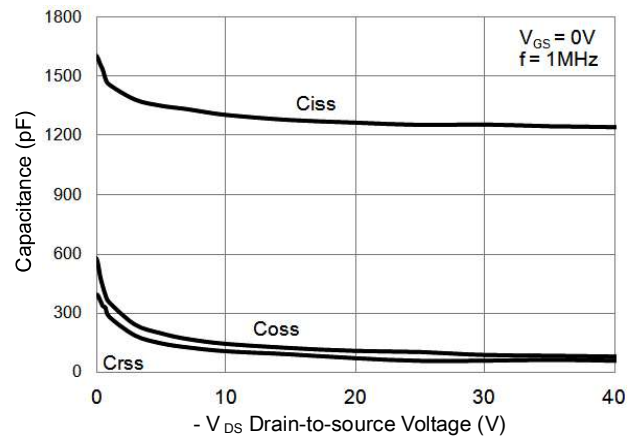


Fig.8 Capacitance Characteristics

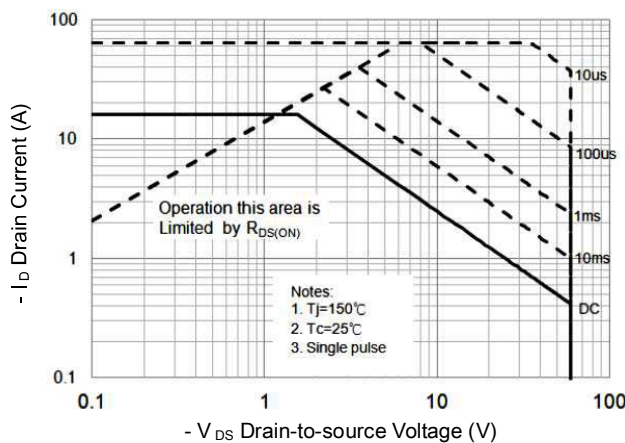


Fig.9 Safe Operating Area

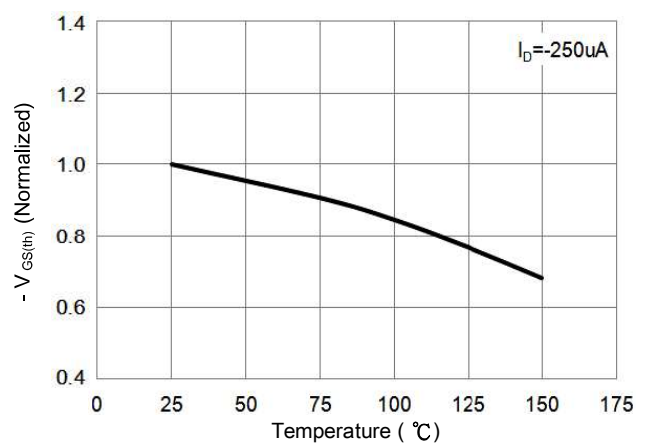


Fig.10 Normalized $V_{GS(th)}$ vs. Temperature

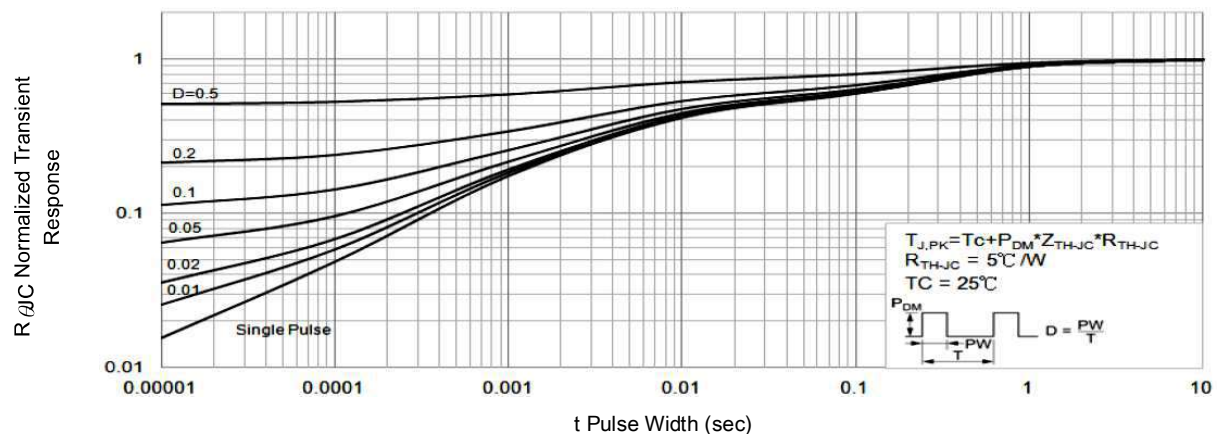
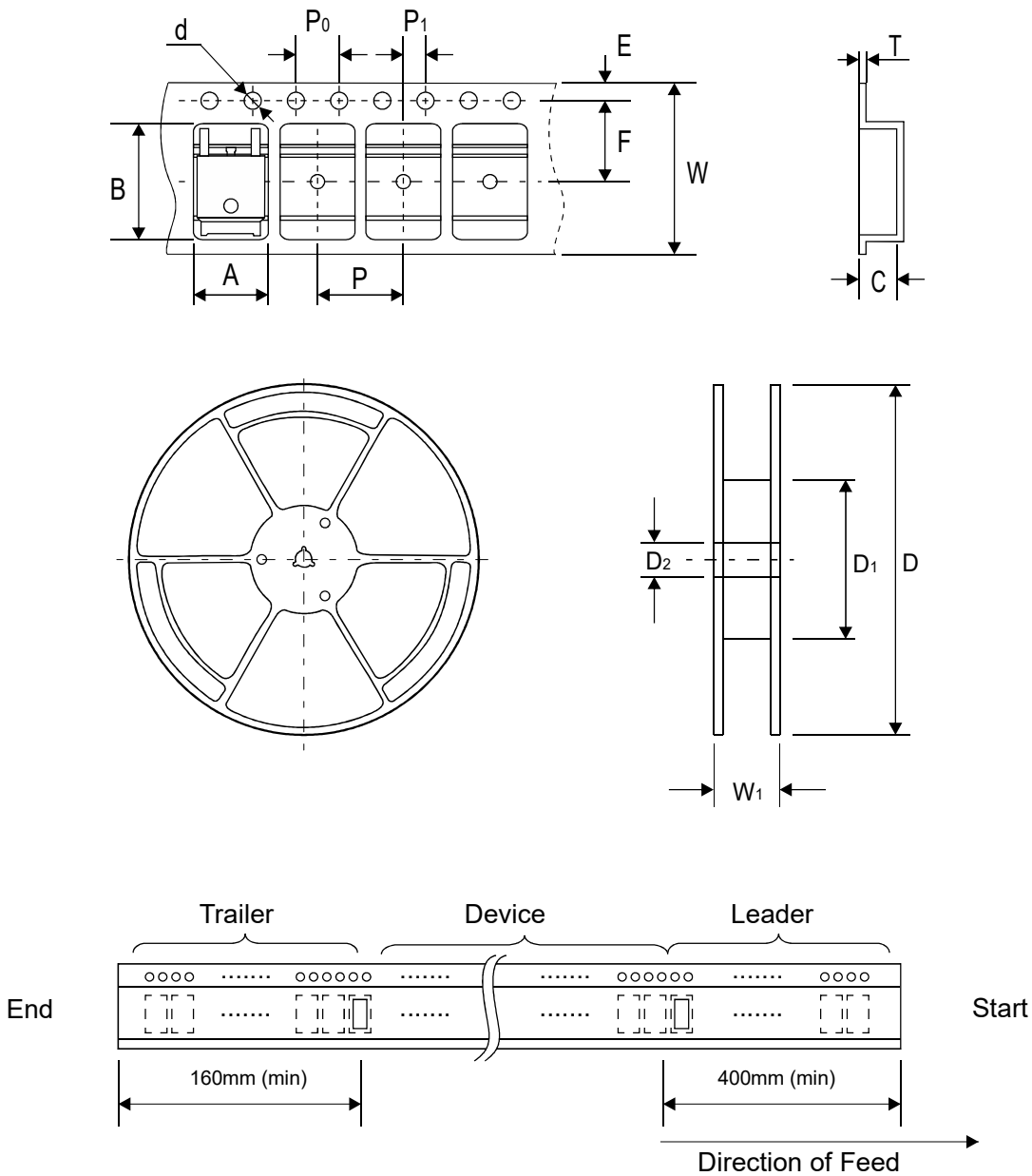


Fig.11 Normalized Maximum Transient Thermal Impedance
Normalized Transient Thermal Impedance

Reel Taping Specification

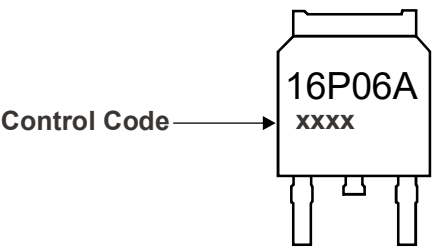


TO-252 (D-PAK)	SYMBOL	A	B	C	d	D	D1	D2
	(mm)	6.90 ± 0.10	10.50 ± 0.10	2.70 ± 0.10	1.55 ± 0.05	330.00 ± 2.00	100.00 ± 1.00	13.00 ± 1.00
	(inch)	0.272 ± 0.004	0.413 ± 0.004	0.106 ± 0.004	0.061 ± 0.002	12.992 ± 0.079	3.937 ± 0.039	0.512 ± 0.039

TO-252 (D-PAK)	SYMBOL	E	F	P	P ₀	P ₁	T	W	W ₁
	(mm)	1.75 ± 0.10	7.50 ± 0.10	8.00 ± 0.10	4.00 ± 0.10	2.00 ± 0.10	0.30 ± 0.05	16.00 ± 0.10	21.00 ± 1.00
	(inch)	0.069 ± 0.004	0.295 ± 0.004	0.315 ± 0.004	0.157 ± 0.004	0.079 ± 0.004	0.012 ± 0.002	0.630 ± 0.004	0.827 ± 0.039

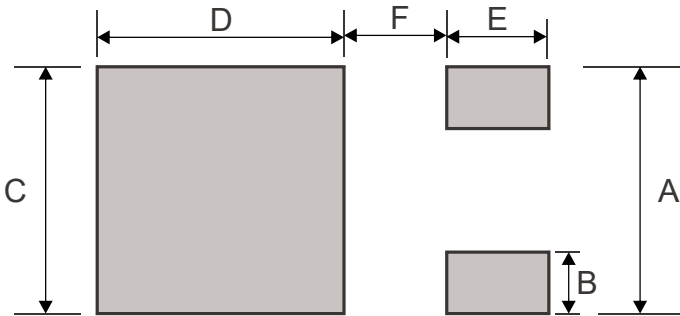
Marking Code

Part Number	Marking Code
CMS16P06D-HF	16P06A



Suggested PAD Layout

SIZE	TO-252 / DPAK	
	(mm)	(inch)
A	6.17	0.243
B	1.60	0.063
C	5.80	0.228
D	6.20	0.244
E	3.00	0.118
F	2.58	0.101



Standard Packaging

Case Type	REEL PACK	
	REEL (pcs)	REEL SIZE (inch)
TO-252/D-PAK	2,500	13